



PNP Silicon Epitaxial Planar Transistor

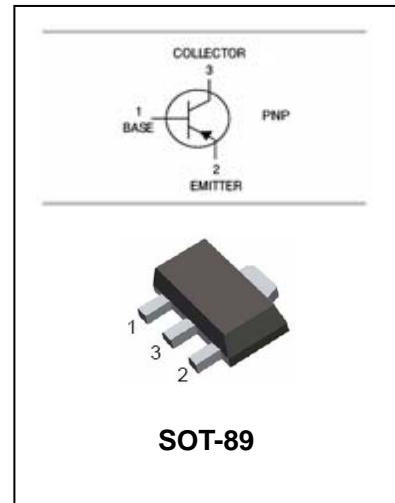
KTB1124

FEATURES

- Adoption of MBIT processes.
- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Complementary: KTD1624.



Lead-free



ORDERING INFORMATION

Type No.	Marking	Package Code
KTB1124	XA/XB/XC	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-3	A
I _{CP}	Collector Current –Continuous(Pulse)	-6	A
P _C	Collector Dissipation	1	W
T _j , T _{stg}	Junction and Storage Temperature	-55 to +150	°C



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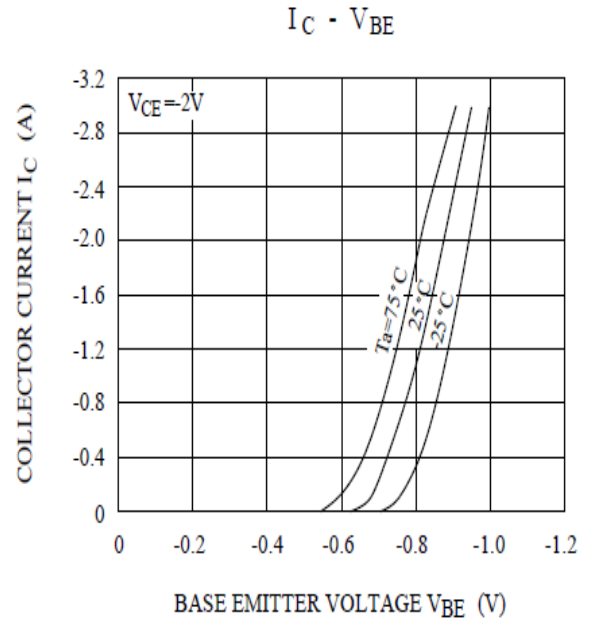
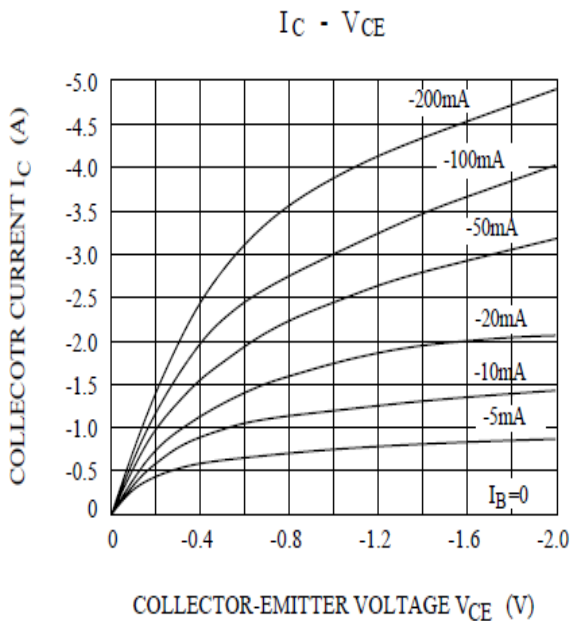
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-100ma$	100		400	
		$V_{CE}=-2V, I_C=-3A$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.1A$		-0.35	-0.7	V
Base-emitter voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.1A$		-0.94	-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		39		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C
Range	100-200	140-280	200-400

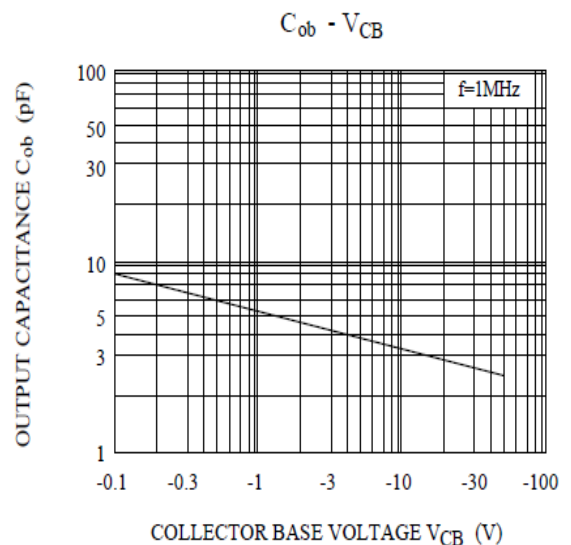
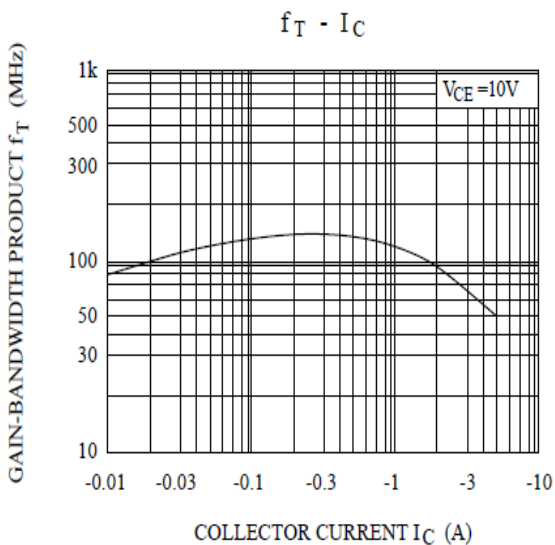
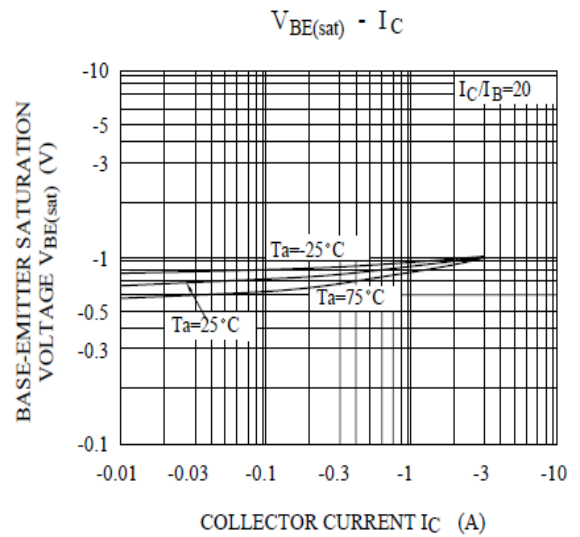
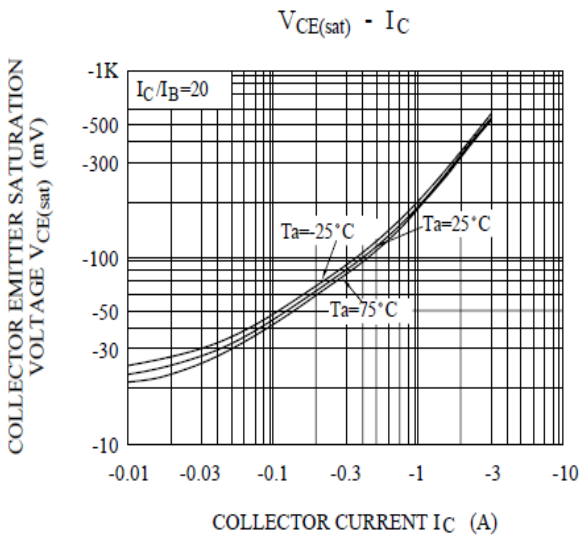
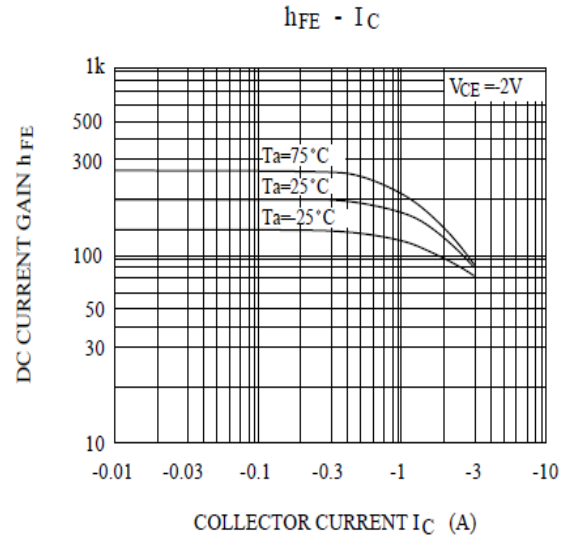
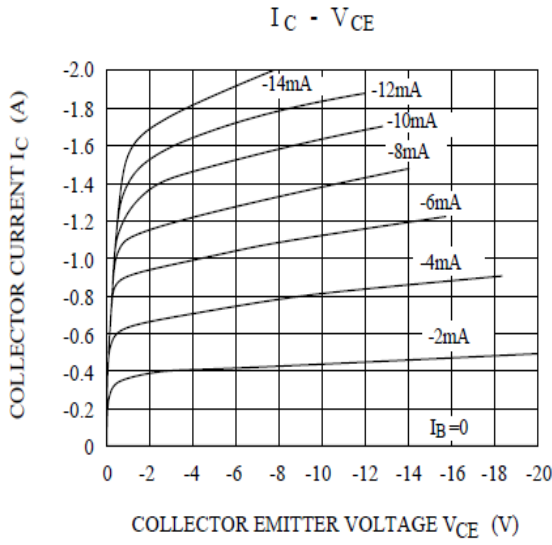
TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





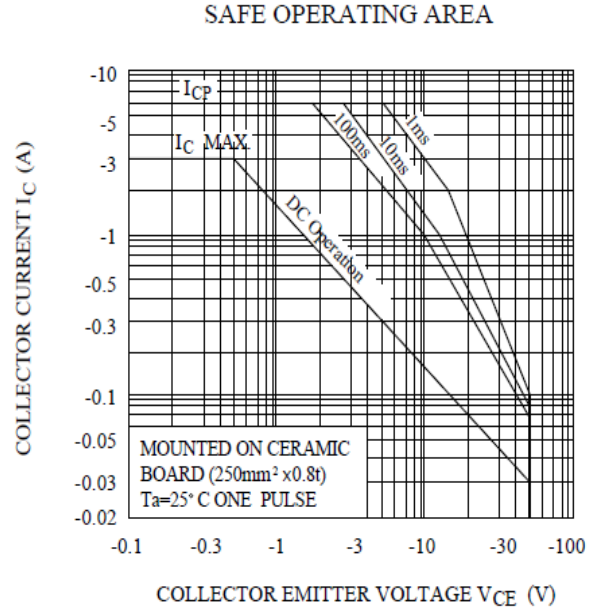
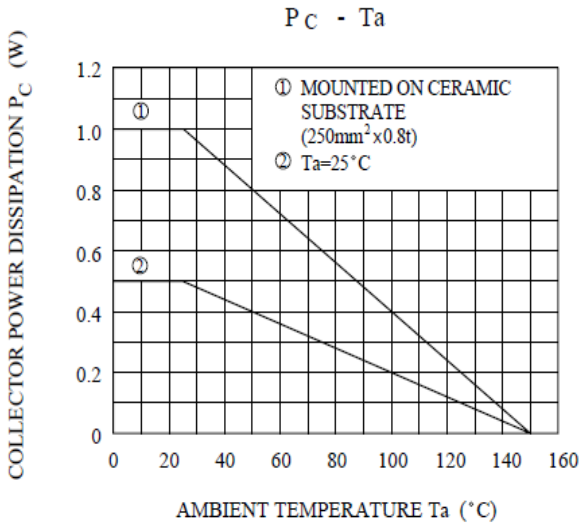
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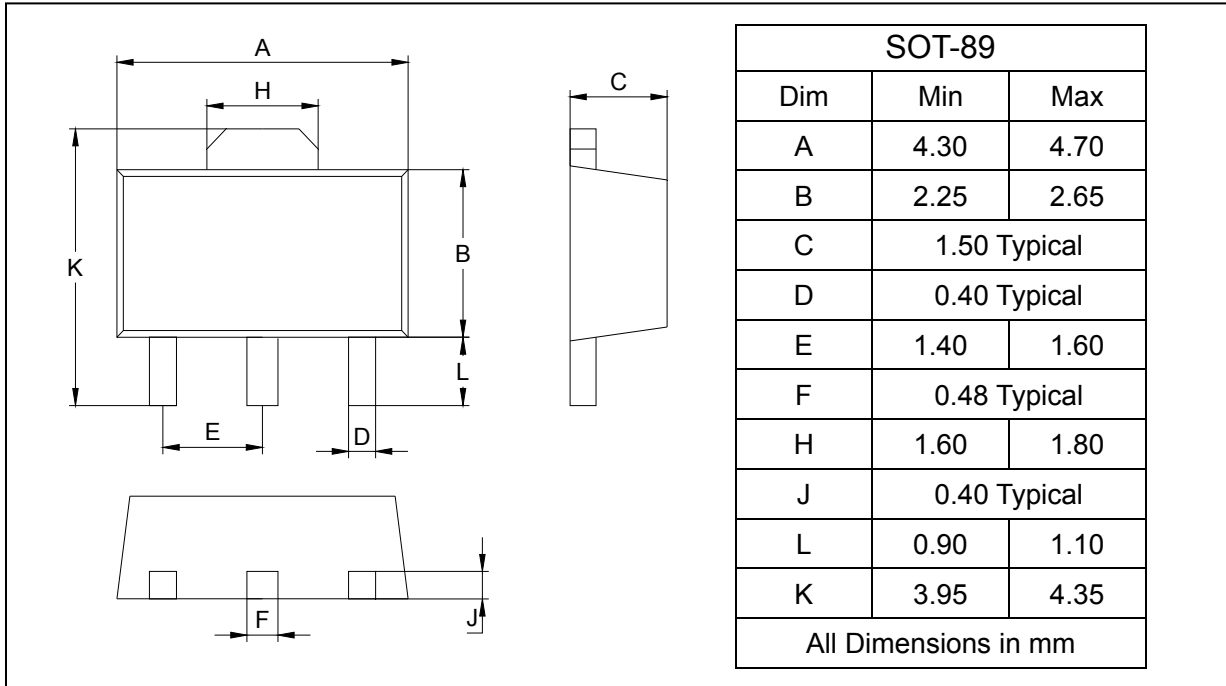
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PACKAGE OUTLINE

Plastic surface mounted package

SOT-89

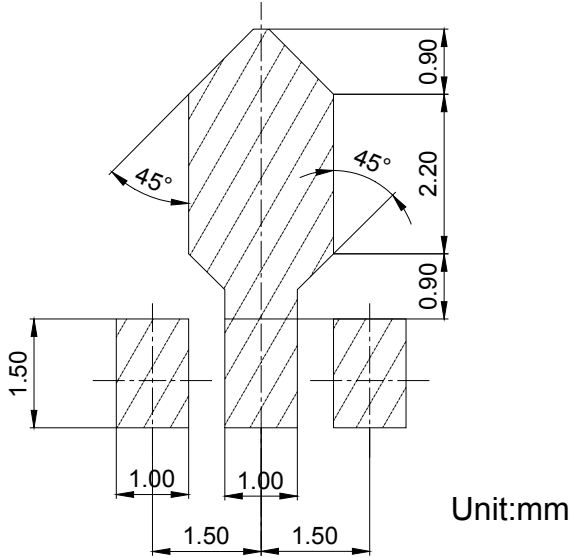




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SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTB1124	SOT-89	1000/Tape&Reel